MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK16G60W

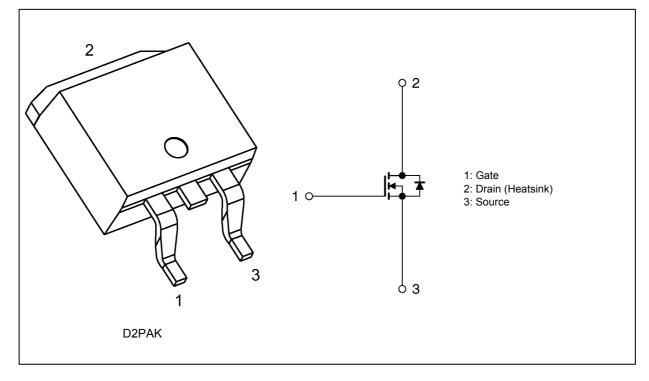
1. Applications

Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.16 \Omega$ (typ.) by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: $V_{\rm th}$ = 2.7 to 3.7 V (V_{\rm DS} = 10 V, $I_{\rm D}$ = 0.79 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	600	V
Gate-source voltage		V _{GSS}	±30	
Drain current (DC)	(Note 1)	Ι _D	15.8	Α
Drain current (pulsed)	(Note 1)	I _{DP}	63.2	
Power dissipation (T _c	= 25°C)	PD	130	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	194	mJ
Avalanche current		I _{AR}	4.0	A
Reverse drain current (DC)	(Note 1)	I _{DR}	15.8	
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	63.2	
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Мах	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.962	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_DD = 90 V, T_ch = 25°C (initial), L = 21.2 mH, R_G = 25 Ω , I_AR = 4.0 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

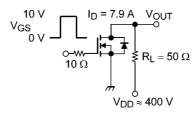
6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	600	—	—	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.79 mA	2.7	_	3.7	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 7.9 A		0.16	0.19	Ω

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 1 MHz	_	1350	_	pF
Reverse transfer capacitance	C _{rss}]		4	_	
Output capacitance	C _{oss}	1		35	_	
Effective output capacitance	C _{o(er)}	V_{DS} = 0 to 400 V, V_{GS} = 0 V		55	_	
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz		6	_	Ω
Switching time (rise time)	t _r	See Figure 6.2.1		25	_	ns
Switching time (turn-on time)	t _{on}]		50	_	
Switching time (fall time)	t _f]		5	_	
Switching time (turn-off time)	t _{off}]		100		
MOSFET dv/dt ruggedness	dv/dt	V _{DD} = 0 to 400 V, I _D = 7.9 A	50	_	_	V/ns



Duty \leq 1%, $t_W =$ 10 μs

Fig. 6.2.1 Switching Time Test Circuit

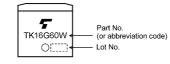
6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, V_{GS} \text{ = } 10 \text{ V}, \text{I}_{D} \text{ = } 15.8 \text{ A}$	_	38	—	nC
Gate-source charge 1	Q _{gs1}		_	9	—	
Gate-drain charge	Q _{gd}		_	16	_	

6.4. Source-Drain Characteristics (Ta = 25°C unless otherwise specified)

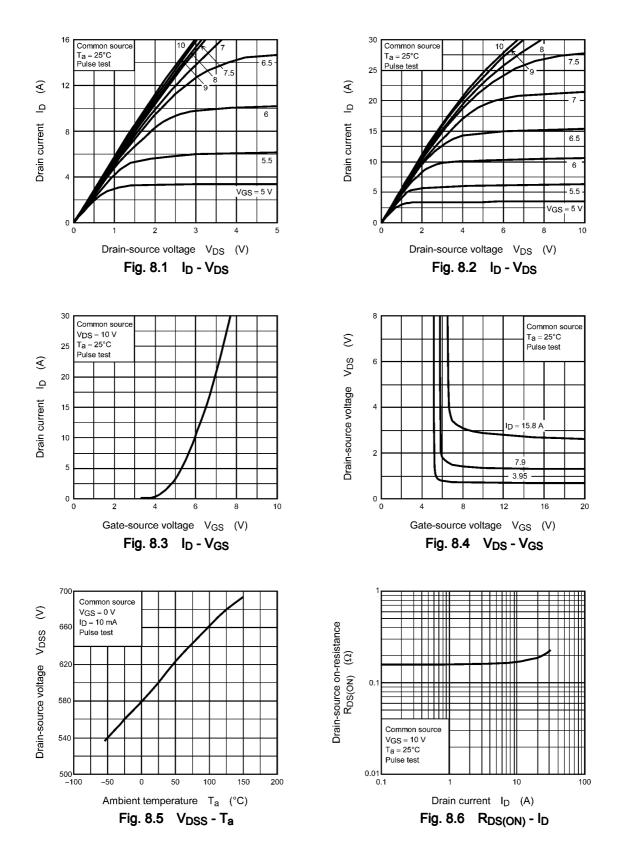
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 15.8 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 7.9 A, V _{GS} = 0 V	_	280	_	ns
Reverse recovery charge	Q _{rr}	-dI _{DR} /dt = 100 A/μs	_	2.9	_	μC
Peak reverse recovery current	I _{rr}		_	23	_	А
Diode dv/dt ruggedness	dv/dt	I_{DR} = 7.9 A, V_{GS} = 0 V, V_{DD} = 400 V	15		_	V/ns

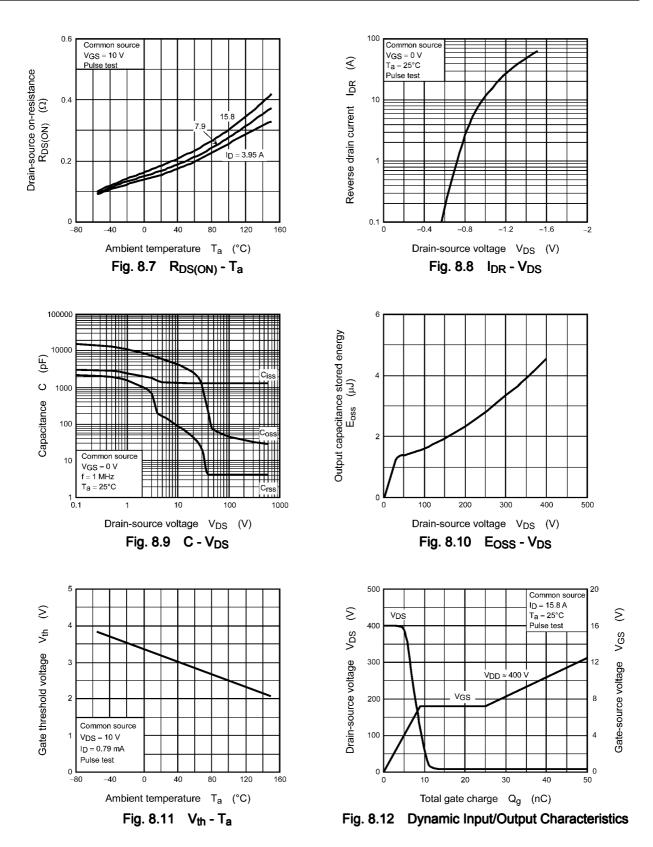
7. Marking



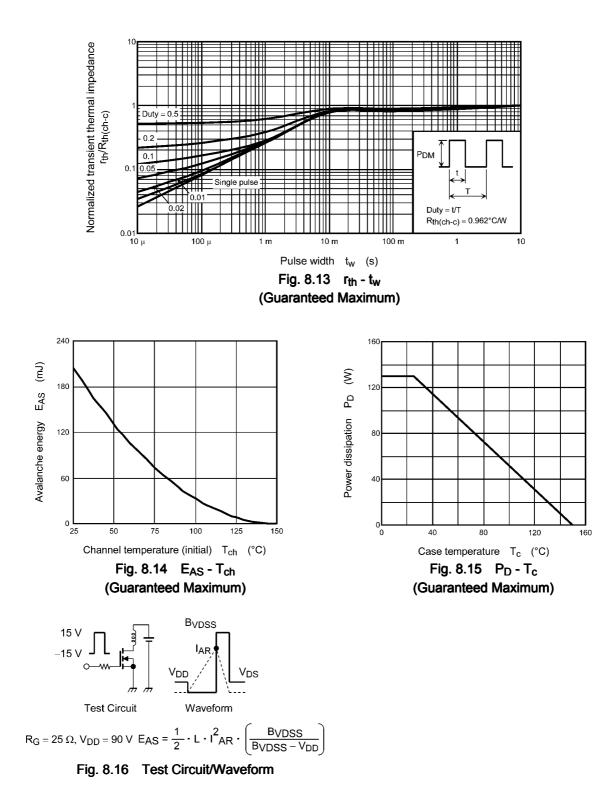


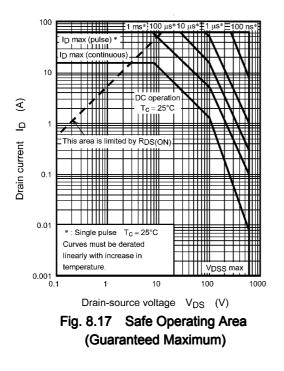
8. Characteristics Curves (Note)









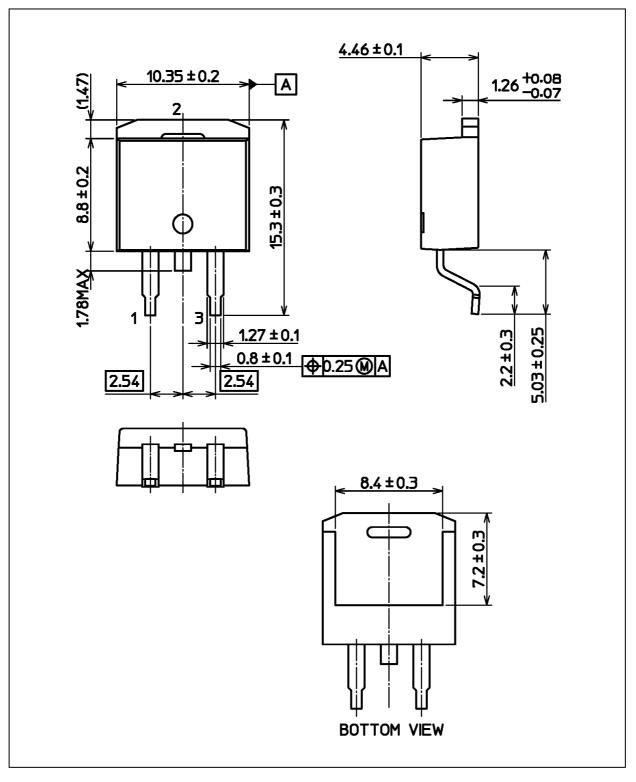


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm





Package Name(s)

TOSHIBA: 2-11H1A

Nickname: D2PAK

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